

## Amendments to the Specification:

Please amend the paragraph bridging pages 12 and 13 as follows:

Referring now to Fig. 3, there is shown a cross section of a first solder bump that has been created in accordance with the above referenced related application, this drawing has been extracted from the related application for reference purposes. The elements that are shown in Fig. 3 that form part of the solder bump of the related application are the following:

- 10, a semiconductor surface such as the surface of a substrate
- 30, a layer of dielectric that has been deposited over the semiconductor surface 10
- 32, contact pads that have been created on the surface of the layer 30 of dielectric
- 34, a patterned layer of passivation that has been deposited over the surface of the layer 30 of dielectric; openings have been created in the layer 34 of passivation, partially exposing the surface of contact pads 32
- 36, an isotropically etched layer of barrier metal; because this layer of barrier metal has been isotropically etched, the barrier metal has been completely removed from the surface of the layer 34 of passivation except where the barrier metal is covered by the overlying pillar metal (38) of the solder bump
- 38, the pillar metal of the solder bump
- 40, a layer of under bump metal created overlying the pillar metal 38 of the solder bump, wherein the distance between an edge of the under bump metal layer and an edge of the metal pillar of the solder bump is greater than 0.2 microns
- 42, the solder metal.